

| | | | | |
|-----------------------------------|---------------------------------------|--|---|-------------|
| Notice of References Cited | Application/Control No. 10/521,227 | | Applicant(s)/Patent Under Reexamination DAY, IAN EDWARD | |
| | Examiner Eric Wong | | Art Unit 2883 | Page 1 of 1 |

U.S. PATENT DOCUMENTS

| * | | Document Number Country Code-Number-Kind Code | Date MM-YYYY | Name | Classification |
|---|---|--|-----------------|------------------|----------------|
| * | A | US-2006/0039666 | 02-2006 | Knights et al. | 385/129 |
| * | B | US-2005/0123227 | 06-2005 | Vonsovici et al. | 385/002 |
| * | C | US-6,801,702 | 10-2004 | Day, Ian Edward | 385/130 |
| * | D | US-7,020,371 | 03-2006 | Logvin et al. | 385/129 |
| | E | US- | | | |
| | F | US- | | | |
| | G | US- | | | |
| | H | US- | | | |
| | I | US- | | | |
| | J | US- | | | |
| | K | US- | | | |
| | L | US- | | | |
| | M | US- | | | |

FOREIGN PATENT DOCUMENTS

| * | | Document Number Country Code-Number-Kind Code | Date MM-YYYY | Country | Name | Classification |
|---|---|--|-----------------|---------|------|----------------|
| | N | | | | | |
| | O | | | | | |
| | P | | | | | |
| | Q | | | | | |
| | R | | | | | |
| | S | | | | | |
| | T | | | | | |

NON-PATENT DOCUMENTS

| * | | Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages) |
|---|---|---|
| | U | HEWITT P D ET AL, Improved modulation performance of a silicon p-i-n device by trench isolation, March 2001, Journal of Lightwave Technology IEEE, vol.19 no.3, pages 387-390 |
| | V | |
| | W | |
| | X | |

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.